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Sheet 1 of 1

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MI22-1657SERIAL NO.
09 955,320

LIST OF ART CITED BY APPLICANT

Use separate sheet if necessary



APPLICANT: Cam Bascen et al

FILING DATE
July 13, 2001GROUP
1762

U.S. PATENT DOCUMENTS

Examiner Name		Document Number	Date	Country	Class	Success	Filing Date of Application
EF		1	2001-07-13	USA			
		2					
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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Success	Translation	
							Yes	No

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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	A2	
	A3	

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EXAMINER

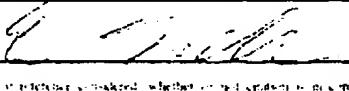
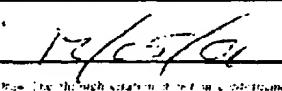
DATE CONSIDERED

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8/29/01

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AUG 29 2001 LIST OF ART CITED BY APPLICANT See General Index for Abbreviations				ATTY. DOCKET NO. M122-1687	SERIAL NO. 09/663,220			
				APPLICANT John Boscari et al.				
				FILED DATE Aug 29, 2001	GROUP I			
U.S. PATENT DOCUMENTS								
Document Number		Document Number	Date	Name		Class	Subclass	Flag Date of Application
		AN						
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FOREIGN PATENT DOCUMENTS								
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							Yes	No
		AL						
		AM						
		AN						
		AG						
		AP						
OTHER REFERENCES (including Author, Title, Date, Permit/Pages, Etc.)								
	AB	Kam et al. Structural and Electrical Properties of BaTiO_3 grown on $\mu\text{-InP}$ (100) by low-pressure metalorganic chemical vapor deposition at low temperature. Applied Physics Letters, Vol. 65, No. 15, 10/09/94, pp. 1955-1957						
	AN							
	AM							
EXAMINER				DATE CONSIDERED				
EXAMINER: Initials of reference considered, whether or not evidence in compliance with 35 U.S.C. 102. The following statement is for a reference and is not considered to be a finding with respect to patentability of the application.								

<p style="text-align: center;">U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE AUG 29 2001 LIST OF ART CITED BY APPLICANT U.S. GOVERNMENT PRINTING OFFICE</p>				ATTY. DOCKET NO. A22267	SERIAL NO. 09/665,220					
				APPLICANT TOMIKA, KAZUO						
				ELIST DATE JUL 15, 2001	GROUP 1					
U.S. PATENT DOCUMENTS										
Reference Number		Document Number	Date	Note		Class	Subclass	Using this Reference		
	AA									
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	AL									
	AM									
	AS									
	AO									
	AP									
OTHER REFERENCES (including Author, Title, Date, Periodic, Page, Etc.)										
EF	AB	S. Yamada et al., Abstract, <i>Re + S-Tc ratio dependency of the dielectric properties for the α-Si_x film thin film prepared by ion beam sputtering</i> , <i>64 Applied Physics Letters</i> , No. 13, pp. 1622-1626 (1994)						Yes	No	
		M. Yamada et al., Abstract, <i>Thermal-Insulation Spectroscopy of the α-Si_x Thin Film Prepared by Chemical-Vapor-Deposition</i> , <i>31 Jpn. J. on Appl. Phys.</i> , Pt. 1, No. 2A, pp. 726-728 (1992)								
EF	AS	S. Yamada et al., <i>Formation of α-Si_x Films on Si-Li Wires by Chemical-vapor-Deposition</i> , <i>14 Journal of Applied Physics</i> , Vol. 35, No. 9B, Part 2, pp. 4873-4876						Yes	No	
		S. Yamada et al., <i>Formation of α-Si_x Film on Si-Li Wires by Chemical-vapor-Deposition</i> , <i>14 Journal of Applied Physics</i> , Vol. 35, No. 9B, Part 2, pp. 4873-4876								
EXAMINER	<i>[Signature]</i>			DATE CONSIDERED					<i>[Signature]</i>	
<p>EXAMINER Total of references considered, whether cited or not, is in accordance with MPEP 609. Draw line through statement if not in accordance and not considered. Total of references cited with text in the body of the application.</p>										

<p style="text-align: center;">AUG 25 2001 LIST OF ART CITED BY APPLICANT The United States Patent and Trademark Office</p>			U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. AB22-347	SERIAL NO. 10/004,520	
			APPLICANT Cen Research, Inc.		FILING DATE Jul 15, 2000		
			GK-48 US-004		GK-48 US-004		
			U.S. PATENT DOCUMENTS				
Examiner Initials	Document Number	Date	Name		Class	Subclass	Filing Date or Application
AS							
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FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country	Class	Subclass	Translation	
AL						Yes	No
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OTHER REFERENCES (including Author, Title, Date, Patent, Paper, Etc.)							
EF	AS	Takashi Kawahara et al., (Ba, SrTiO ₃) Films Prepared by Liquid Source Chemical Vapor Deposition on Ru Electrodes, 35 JES 2.					
		Adv. Phys. Pt. 1, No. 9B, pp. 4880, 4883 (1996).					
EF	AS	Rakesh Khomkar et al., A Novel Low-Temperature Process for Bulk Dielectric Constant BST Thin Films for TMR DRAM Applications, Microelectronics Research Center, Univ. of Texas at Austin, TX (Undated), 2 pages.					
EF	AF	Yong-Tae Kim et al., Abstract, Advantages of Ru/Ti, Indium electrode on the dielectric and leakage characteristics of Ba-Sr-TiO ₃ capacitor, 35 JES 1, Adv. Phys. Pt. 1, No. 12A, pp. 6153-6156 (2000).					
EXAMINER	<i>C. L. C.</i>		DATE CONSIDERED		10/05/01		

EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP (6). Draw line through citation if not in conformance and not considered. Indicate copy or the type of work (communication or application).

Form PTO-17 LIST OF ART CITED BY APPLICANT <small>U.S. GOVERNMENT PRINTING OFFICE</small> AUG 29 2001			U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. FEE RECEIVED NO. M22-265	SERIAL NO. 09/965,320	
			APPLICANT John K. Kosters et al.				
			FILING DATE July 13, 2001		GROUP 1		
U.S. PATENT DOCUMENTS							
Document Number	Date	Document Number	Date	Number	Class	Subclass	String Date P. Appl. Date
AA							
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FOREIGN PATENT DOCUMENTS							
	Document Number	Date	Country		Class	Subclass	Translated Yes No
AL							
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AP							
OTHER REFERENCES (including Author, Title, Date, Patent, Page, etc.)							
EF	AR	S.H. Park et al. Abstract, Characterization of MIS capacitor of TFT thin film deposited on Si in RF magnetron sputtering					Yes
		TosohDKS, Thin Film V, Sung-sung, San Francisco, CA, pp. 33-39 (April 7, 1995)					
EF	AS	N. Takemoto et al. Abstract, Effect of micro atmosphere on the color, luminance and contrast of TFT-LCD, 98 SID					Yes
		SID Abstracts, Kyoto/Gamagori, Japan, No. 98-13, pp. 339-350 (1998)					
EF	MI	H. Yamashita et al. Abstract, Resistive composition methods and characterization of TFT, TFT-LCD pixels, IBM, International Symposium on Applications of Ferroelectrics, Cincinnati, OH, pp. 285-288 (August 2, 1992)					Yes
EXAMINER	<i>C. Tschetter</i>		DATE CONSIDERED 12/15/01				
EXAMINER: Initial of reference considered, whether or not claimed in conformance with MPEP 609. Draw line through entries not in conformance and not considered Include with other communications to applicant							

7/13/01

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Sheet 1 of 1

Form PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO
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UNNUMBERED

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LIST OF ART CITED BY APPLICANT
Use several sheets if necessary.APPLICANT
Com-Baster et al

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FILING DATE
09/02/2001GROUP
UNCLASSIFIED

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07/13/01
09/05/2001

U.S. PATENT DOCUMENTS

Examiner		Document Number	Date	Name	Class	Subclass	Filing Date or Application Date
CC	AK			Com-Baster et al as filed			Filed Continuation
CC	AB	09475518		Com-Baster et al as filed and as amended			01/03/00
CC	AC	09500723		Com-Baster et al as filed			09/26/00
CC	AD	09459025	10/17/00	Tomizawa et al	301	3213	
CC	AE	09410751	06/08/01	Eguchi et al	438	785	
	AF						
	AG						
	AH						
	AI						
	AJ						
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FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						VPA	No

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER

J. L. B.

DATE CONSIDERED

12/04/01

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<p style="text-align: center;">U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT 1000 Leavenworth Street, Washington, D.C. 20591 RECEIVED APR 25 2001</p>				APPLY DOCKET NO. M222585		SERIAL NO. 09/633,250	
				APPLICANT C. M. Baskaran et al.		FILING DATE JUN 12, 2000	
				GROUP I		CLASS 148	
				U.S. PATENT DOCUMENTS			
Reference Number		Document Number	Date	Author	Class	Subclass	Group Date In Application
	AN	5,256,433	07/26/93	Nakamura			
	AB	5,751,944	06/23/97	Endo			
	AC	5,776,254	03/24/98	Yoshio et al			
	AD	5,783,251	03/10/98	Yoshio et al			
	AE	5,798,913	07/21/98	Reh			
	AF	6,043,326	08/25/98	Okamura et al			
	AG	6,046,342	02/28/98	Ochiai			
	AH	6,078,392	01/01/00	Kakihara et al			
	AI	6,155,815	09/26/00	Huang et al			
	AJ	6,103,598	11/28/00	Watanabe			
	AK	6,057,203	03/14/98	Hab et al			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes No
	AL	0,240,714 A2	26/01/98	EPO - Zhou et al, Applied Materials, Inc.			
	AM	0,937,322 A2	12/05/99	EPO - Ueda, Matsuda, Matsuda Electric Ind. Co.			
	AN	WO 98/29497	20/02/98	WIPO - Simpson, John et al			
	AO	0,424,120 A1	30/08/91	EPO - Kamvana, Samsi et al, NEC Corporation			
	AP	WO 99/04655	11/06/99	WIPO - Narwakar et al, Applied Materials, Inc.			
OTHER REFERENCES (including Author, Date, Date, Patent, Page, etc.)							
	AR		Steve Baskaran et al, <i>Composition Dependence of the Dielectric Properties of MOxSiO_x RRAM</i> , IEDM, pp. 1-21 (M22-148)				
			Meeting 12/01/98				
	AS		Steve M. Baskaran et al, <i>MOxSiO_x RRAM for High Density DRAM Applications</i> , Report to SEMICONWEST 07/12/98, 2 pages				
	AL		Y.C. Chen et al, <i>Abstract, Improvement in the Properties of Chemical Vapors Deposited Glass for Interconnects Through Use of a Self</i>				
			Layer				
EXAMINER	<i>C. J. Chen</i>			DATE CONSIDERED <i>1/26/01</i>			
<p>CLAIMANT - Initials of referee considered whether or not claim is in accordance with 35 U.S.C. 101. This may also be used in other claim and not a legend for the entire document with each claim and its corresponding examiner.</p>							

<p style="text-align: center;">U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p style="text-align: center;">LIST OF ART CITED BY APPLICANT For Patent Application</p> <p style="text-align: center;">AUG 29 2001</p>				ATTY. DOCKET NO. M22-1657	SERIAL NO. 10/306,320		
				APPLICANT Cao, Baotian et al.			
				FLING DATE Aug 29, 2001	CLASS 148		
U.S. PATENT DOCUMENTS							
Examiner Name	Ref.	Document Number	Date	Name	Class	Subclass	Filing Date of Appl. prior
EF	AN	5,476,396	11/28/98	Shen et al.			
EF	AN	5,254,506	10/19/93	Kameyama			
EF	AN	6,156,626	12/08/00	Agarwal et al.			
EF	AN	6,165,334	12/26/00	Agarwal et al.			
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	AN						Yes
	AN						No
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OTHER REFERENCES (including Author, Title, Date, Patent, Page, Etc.)							
EF	AN	Cheng-Ming Chu et al., Abstract: Electrical properties and crystal structure of the SrRuO ₃ film prepared at low temperature					
		on a LaAlO ₃ electrode by radio-frequency sputtering. - 70 APPLIED PHYSICS LETTERS No. 2, pp. 249-251 (1997)					
EF	AN	Kazuhiko Iguchi et al., Abstract: Chemical vapor deposition of the SrTiO ₃ film layer for application in electric cells					
		dynamic random access memory. 14 INTEGRATED ELECTRONICS No. 1-4, Pt. 1, pp. 33-42 (1997)					
EF	AN	Q-X. Jia et al., Abstract: Structural and electronic properties of Ru-Sr ₂ Sn ₃ thin films with an RuO ₂ bottom electrode					
		29 INTEGRATED ELECTRONICS No. 1-4, pp. 111-119 (1998)					
EXAMINER				DATE CONSIDERED 12/05/01			
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Form PTO-1660		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1857	SERIAL NO. 09/905,320		
LIST OF ART CITED BY APPLICANT (use several sheets if necessary)				APPLICANT: Cam Basceri et al.			
				FILING DATE July 13, 2001	GROUP 1762		
U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Applicable
EF	AA	5,590,314	01-1997	Geir	357	300	
	AB						
EF	AC	08744,988		Appended to H (No Date, and converted to transmittal to Patent Office Austin, 155000 Office Action, and 112881 Other Action)			August 26, 1998
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
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EXAMINER <i>En Felt</i>		DATE CONSIDERED 9/30/02					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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REVIEW: *Long-term effects of a low-carbohydrate diet on blood lipoproteins, blood pressure, and blood glucose in type 2 diabetes*. *Diabetes Care* 2005; 28: 2491-2497.

